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J. Antis

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Chin-Yang Chen Examiner: WEISS, HOWARD.
5 Filing Date: 10/01/2001 Art Unit: 2814
Serial No.: 09/682,628 Docket No.: NAUP0384USA

Title: AN ANTI-FUSE STRUCTURE WITH LOW ON-STATE
RESISTANCE AND LOW OFF-STATE LEAKAGE

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To: Assistant Commissioner for Patents
Washington, D.C. 20231

Subject: Reply to Office action dated 07/03/2002

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Dear Sir:

OCT 1 - 2002

AMENDMENT

TECHNOLOGY CENTER 2800

20 In response to the Office action noted above, please
amend the above-identified application as follows:

In the specification:

Please substitute the paragraph [0021] from page
5, with the following paragraph:

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Please refer to Fig.3 to Fig.6 of schematic
diagrams of several embodiments of an anti-fuse
structure according the present invention. A
semiconductor wafer 50 comprises a silicon substrate
52. An isolation layer 54 is positioned on the silicon
substrate 52 and an anti-fuse structure 51 is set
on the isolation layer 54. The anti-fuse structure

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